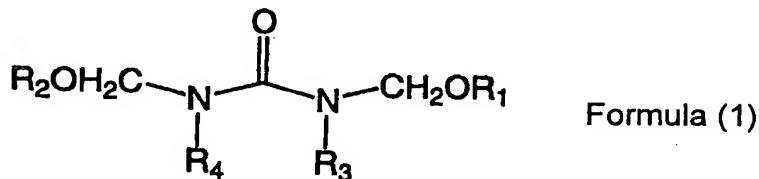


**AMENDMENTS TO THE CLAIMS:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Original) A composition for forming anti-reflective coating characterized by containing a compound of formula (1)



wherein R<sub>1</sub> and R<sub>2</sub> are independently of each other hydrogen atom or an alkyl group, R<sub>3</sub> and R<sub>4</sub> are independently of each other hydrogen atom, methyl group, ethyl group, hydroxymethyl group or an alkoxyethyl group.

2. (Original) A composition for forming anti-reflective coating characterized by containing a resin produced from the compound of formula (1) according to claim 1.

3. (Original) The composition for forming anti-reflective coating according to claim 2, wherein the resin is a condensation product produced from the compound of formula (1).

4. (Currently Amended) The composition for forming anti-reflective coating according to ~~any one of claims 1 to 3~~ claim 1, further containing a light absorbing compound and/or a light absorbing resin.

5. (Original) The composition for forming anti-reflective coating according to claim 4, wherein the light absorbing compound is at least one compound selected from naphthalene compounds and anthracene compounds.

6. (Original) The composition for forming anti-reflective coating according to claim 4, wherein the light absorbing compound is at least one compound selected from triazine compounds and triazine trione compounds.

7. (Original) The composition for forming anti-reflective coating according to claim 4, wherein the light absorbing resin is a resin having in the structure at least one aromatic ring structure selected from benzene ring, naphthalene ring and anthracene ring.

8. (Currently Amended) The composition for forming anti-reflective coating according to ~~any one of claims 1 to 3~~ claim 1, further containing a resin having at least one crosslink-forming substituent selected from hydroxy group, carboxy group, amino group and thiol group.

9. (Currently Amended) The composition for forming anti-reflective coating according to ~~any one of claims 1 to 3~~ claim 1, further containing an acid and/or acid generator.

10. (Currently Amended) A method of forming an anti-reflective coating for use in a manufacture of a semiconductor device, characterized by comprising the steps of: coating the composition for forming anti-reflective coating according to ~~any one of claims 1 to 3~~ claim 1 on a substrate, and baking it.

11. (Currently Amended) A process for manufacturing a semiconductor device, characterized by comprising the steps of:  
coating the composition for forming anti-reflective coating according to ~~any one of claims 1 to 3~~ claim 1 on a substrate and baking it to form an anti-reflective coating;  
forming a photoresist on the anti-reflective coating;  
exposing the substrate covered with the anti-reflective coating and the photoresist with a light;  
developing it;  
transferring an image on the substrate by etching to form an integrated circuit device.